DME50B01

Silicon PNP epitaxial planar type (Tr1) Silicon NPN epitaxial planar type (Tr2)

For general amplification DME20B01 in SMini5 type package

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)
- Marking Symbol: A3

Basic Part Number

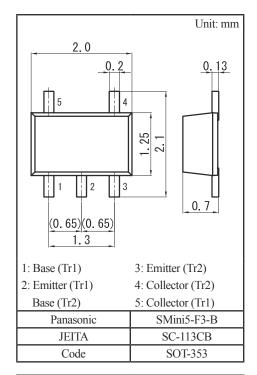
DSA2001 + DSC2001 (Emitterr-base connection)

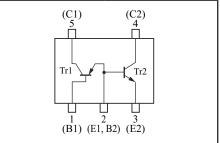
Packaging

DME50B010R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter	Symbol	Rating	Unit	
	Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Tr1	Emitter-base voltage (Collector open)	V _{EBO}	-7	V	
	Collector current	I _C	-100	mA	
	Peak collector current	I _{CP}	-200	mA	
	Collector-base voltage (Emitter open)	V _{CBO}	60	V	
	Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Tr2	Emitter-base voltage (Collector open)	V _{EBO}	7	V	
	Collector current	I _C	100	mA	
	Peak collector current	I _{CP}	200	mA	
	Total power dissipation	P _T	150	mW	
0	Junction temperature	Tj	150	°C	
Overall	Operating ambient temperature	T _{opr}	-40 to +85	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	





Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

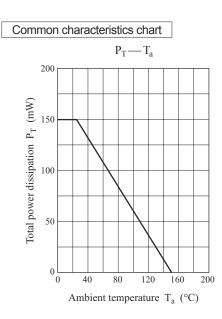
• Tr1

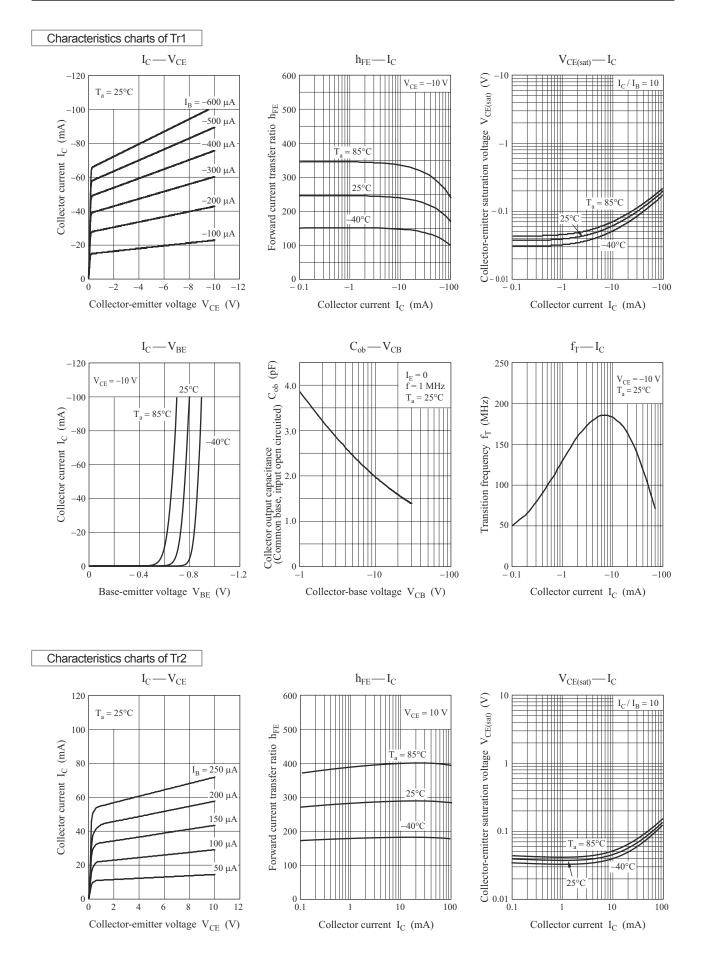
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -10$ V, $I_{\rm B} = 0$			-100	μΑ
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA	210		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$		- 0.2	- 0.5	V
Transition frequency	\mathbf{f}_{T}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

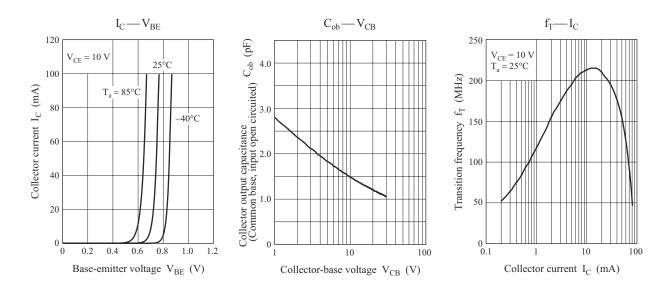
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	210		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_{T}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

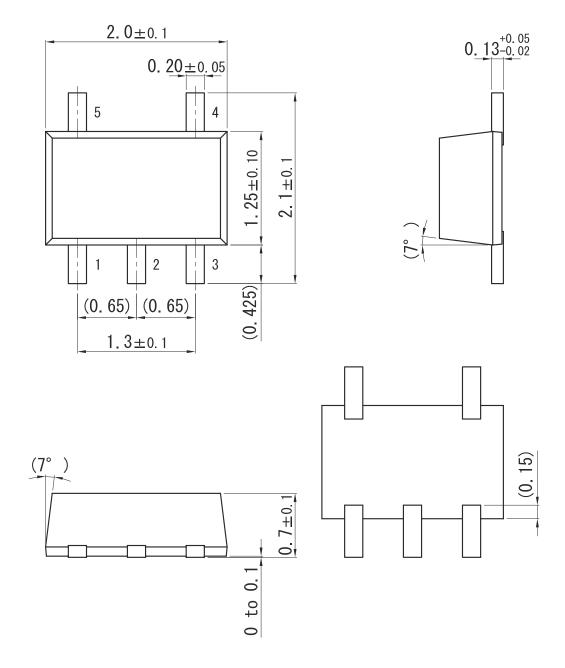




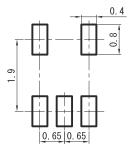


SMini5-F3-B

Unit: mm



Land Pattern (Reference) (Unit: mm)



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